Vishay Semiconductors

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Ultrafast Rectifier, 2 A FRED Pt®



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 A			
V _R	600 V			
V _F at I _F	0.95 V			
t _{rr}	55 ns			
T _J max.	175 °C			
Package	SMF (DO-219AB)			
Circuit configuration	Single			

FEATURES

- Ultrafast recovery time, reduced Q_{rr}, and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM, snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Wave and reflow solderable
- Compatible to SOD-123W package case outline
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art ultrafast recovery rectifiers designed with optimized performance of forward voltage drop, ultrafast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in PFC, boost, lighting, in the AC/DC section of SMPS, freewheeling and clamp diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element and snubbers.

MECHANICAL DATA

Case: SMF (DO-219AB)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per J-STD-002

Polarity: color band denotes cathode end

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V _{RRM}		600	V
Average rectified forward current	I _{F(AV)}	$T_{\rm C} = 135 \ ^{\circ}{\rm C}^{(1)}$	2	А
Non-repetitive peak surge current	I _{FSM}	T_J = 25 °C, 6 ms square pulse	30	A
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +175	°C

Note

 $^{(1)}\,$ Device on PCB with 8 mm x 16 mm soldering lands

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RoHS

COMPLIANT

HALOGEN



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ELECTRICAL SPECIFICATIONS ($T_J = 25 \ ^{\circ}C$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR} , V_{R}	I _R = 100 μA	600	-	-	
Forward voltage	V	I _F = 2 A	-	1.10	1.35	V
Forward voltage	V _F	I _F = 2 A, T _J = 150 °C	-	0.95	1.15	
Reverse leakage current	1	V _R = V _R rated	-	-	3	
neverse leakage current	I _R	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	100	μA
Junction capacitance	CT	V _R = 600 V	-	5	-	pF

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
			õs, V _R = 30 V	-	42	-	
Reverse recovery time	+	$I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr}$	I _F = 0.5 A, I _R = 1 A, I _{rr} = 0.25 A		-	55	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	40	-	ns
		T _J = 125 °C		-	63	-	
Deals recovery ourrent		T _J = 25 °C	l _F = 2 A dI _F /dt = 500 A/μs	-	7.0	-	А
Peak recovery current I _{RRM}	IRRM	$T_{\rm J} = 125 \ ^{\circ}{\rm C}$	$V_{\rm B} = 400 \text{ V}$	-	8.1	-	A
Reverse recovery charge Q	0	T _J = 25 °C		-	140	-	nC
	Qrr	T _J = 125 °C		-	255	-	nc

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	+175	°C
Thermal resistance, junction to mount	R _{thJM}	Device mounted on PCB with 8 mm x 16 mm soldering lands	-	-	15	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Device mounted on PCB with 2 mm x 3.5 mm soldering lands	-	-	130	°C/W
Approvimete weight				0.015		g
Approximate weight				0.0005		oz.
Marking device		Case style SMF (DO-219AB)		М	PU	



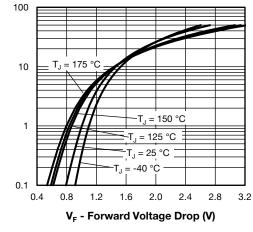


Fig. 1 - Typical Forward Voltage Drop Characteristics

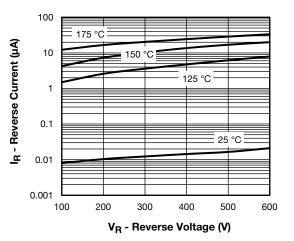


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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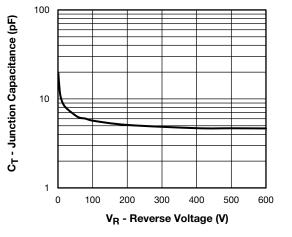
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Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

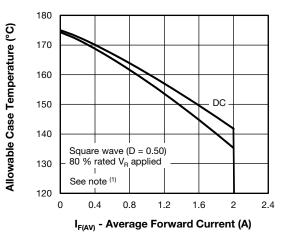


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

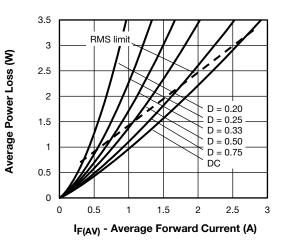


Fig. 5 - Forward Power Loss Characteristics

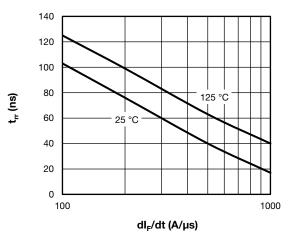
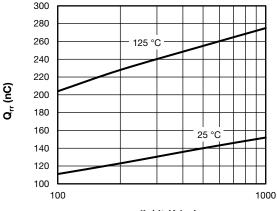


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt



dl_F/dt (A/µs)

Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \, \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ 5); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \, \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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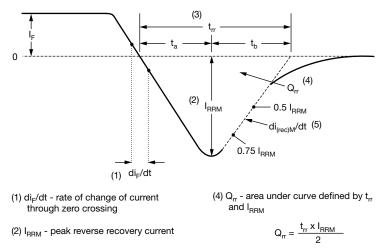
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VS-2EFU06HM3

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(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

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Device code	vs-	2	Е	F	U	06	н	М3
	1	2	3	4	5	6	7	8
	1	- Visl	hay Sen	nicondu	ctors pr	oduct		
	2	- Cur	rent rat	ing (2 =	2 A)			
	3	- Circ	cuit con	figuratio	n:			
		E =	single o	liode				
	4	- F=	SMF pa	ackage				
	5	- Pro	cess ty	ce,				
		U =	ultrafas	st recove	ery			
	6	- Vol	tage co	de (06 =	600 V)			
	7	- H=	AEC-Q	101 qua	lified			
	8	- M3	= halog	en-free,	RoHS-	complia	ant, and	termina

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-2EFU06HM3/I	10 000	10 000	13" diameter plastic tape and reel			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95572			
Part marking information	www.vishay.com/doc?95618			
Packaging information	www.vishay.com/doc?95577			
SPICE model	www.vishay.com/doc?96867			

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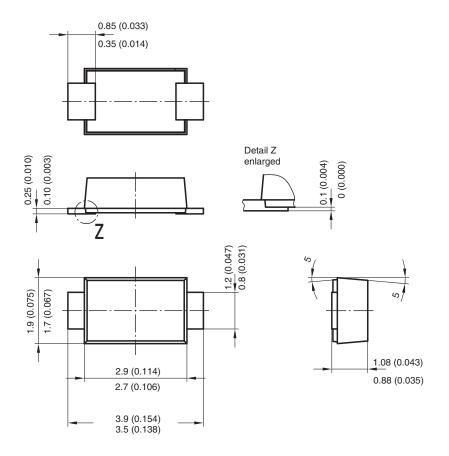
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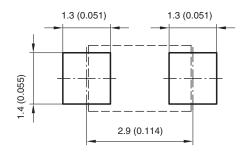
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SMF (DO-219AB)

DIMENSIONS in millimeters (inches)



Foot print recommendation:



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